Dinh Loc Duong

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/4367919/publications.pdf

Version: 2024-02-01

64 papers	4,525 citations	147801 31 h-index	102487 66 g-index
69 all docs	69 docs citations	69 times ranked	8369 citing authors

#	Article	IF	Citations
1	Escalating Ferromagnetic Order via Seâ€Vacancies Near Vanadium in WSe₂ Monolayers. Advanced Materials, 2022, 34, e2106551.	21.0	20
2	Light-emitting Ti₂N (MXene) quantum dots: synthesis, characterization and theoretical calculations. Journal of Materials Chemistry C, 2022, 10, 6508-6514.	5.5	10
3	Probing giant Zeeman shift in vanadium-doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">W</mml:mi><mml:msub><mml:mi>Se</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:m via resonant magnetotunneling transport. Physical Review B, 2021, 103, .	3.2	12
4	Evidence of itinerant holes for long-range magnetic order in the tungsten diselenide semiconductor with vanadium dopants. Physical Review B, 2021, 103, .	3.2	16
5	Lightâ€Controlled Room Temperature Ferromagnetism in Vanadiumâ€Doped Tungsten Disulfide Semiconducting Monolayers. Advanced Electronic Materials, 2021, 7, 2100030.	5.1	17
6	Doping-Mediated Lattice Engineering of Monolayer ReS₂ for Modulating In-Plane Anisotropy of Optical and Transport Properties. ACS Nano, 2021, 15, 13770-13780.	14.6	17
7	Gateâ€Tunable Magnetism via Resonant Seâ€Vacancy Levels in WSe 2. Advanced Science, 2021, , 2102911.	11.2	5
8	Spin-Selective Holeâ€“Exciton Coupling in a V-Doped WSe₂ Ferromagnetic Semiconductor at Room Temperature. ACS Nano, 2021, 15, 20267-20277.	14.6	13
9	Ultrashort Verticalâ€Channel van der Waals Semiconductor Transistors. Advanced Science, 2020, 7, 1902964.	11.2	24
10	Schottky-barrier quantum well in two-dimensional semiconductor nanotransistors. Materials Today Physics, 2020, 15, 100275.	6.0	4
11	Tuning the inhomogeneous charge transport in ZnO interfaces for ultrahigh on/off ratio top-gated field-effect-transistor arrays. Nano Research, 2020, 13, 3033-3040.	10.4	1
12	Layer-controlled single-crystalline graphene film with stacking order via Cuâ€“Si alloy formation. Nature Nanotechnology, 2020, 15, 861-867.	31.5	79
13	Li Intercalation Effects on Interface Resistances of Highâ€Speed and Lowâ€Power WSe 2 Fieldâ€Effect Transistors. Advanced Functional Materials, 2020, 30, 2003688.	14.9	9
14	Gate modulation of the long-range magnetic order in a vanadium-doped WSe2 semiconductor. AIP Advances, 2020, 10, .	1.3	12
15	Ferromagnetic Order at Room Temperature in Monolayer WSe₂ Semiconductor via Vanadium Dopant. Advanced Science, 2020, 7, 1903076.	11.2	148
16	Monodispersed SnS nanoparticles anchored on carbon nanotubes for high-retention sodium-ion batteries. Journal of Materials Chemistry A, 2020, 8, 7861-7869.	10.3	60
17	Carrier transport mechanisms of reactively direct current magnetron sputtered tungsten oxide/n-type crystalline silicon heterojunction. Journal of Power Sources, 2020, 472, 228460.	7.8	5
18	Revealing antiferromagnetic transition of van der Waals MnPS3 via vertical tunneling electrical resistance measurement. APL Materials, 2019, 7, .	5.1	16

#	Article	IF	Citations
19	Proximity Engineering of the van der Waals Interaction in Multilayered Graphene. ACS Applied Materials & Interfaces, 2019, 11, 42528-42533.	8.0	9
20	Ultrahigh Gauge Factor in Graphene/MoS₂ Heterojunction Field Effect Transistor with Variable Schottky Barrier. ACS Nano, 2019, 13, 8392-8400.	14.6	54
21	V₂Se: a novel antifluorite-type cubic phase with a metalâ€“metal bonding. Dalton Transactions, 2019, 48, 8556-8559.	3.3	1
22	Electrically tunable quantum emitters in an ultrathin grapheneâ€“hexagonal boron nitride van der Waals heterostructure. Applied Physics Letters, 2019, 114, .	3.3	23
23	Probing Multiphased Transition in Bulk MoS₂ by Direct Electron Injection. ACS Nano, 2019, 13, 14437-14446.	14.6	29
24	Long-range ferromagnetic ordering in vanadium-doped WSe2 semiconductor. Applied Physics Letters, 2019, 115, .	3.3	31
25	Role of Hole Trap Sites in MoS₂ for Inconsistency in Optical and Electrical Phenomena. ACS Applied Materials & Interfaces, 2018, 10, 10580-10586.	8.0	37
26	van der Waals Metallic Transition Metal Dichalcogenides. Chemical Reviews, 2018, 118, 6297-6336.	47.7	252
27	Raman Characterization of the Charge Density Wave Phase of 1T-TiSe₂: From Bulk to Atomically Thin Layers. ACS Nano, 2017, 11, 1034-1040.	14.6	58
28	Efficient Photothermoelectric Conversion in Lateral Topological Insulator Heterojunctions. Nano Letters, 2017, 17, 214-219.	9.1	28
29	van der Waals Layered Materials: Opportunities and Challenges. ACS Nano, 2017, 11, 11803-11830.	14.6	394
30	Telluriding monolayer MoS2 and WS2 via alkali metal scooter. Nature Communications, 2017, 8, 2163.	12.8	87
31	Stranskiâ€“Krastanov and Volmerâ€“Weber CVD Growth Regimes To Control the Stacking Order in Bilayer Graphene. Nano Letters, 2016, 16, 6403-6410.	9.1	95
32	Hot Carrier Extraction from Multilayer Graphene. Nano Letters, 2016, 16, 6761-6766.	9.1	15
33	High Performance Grapheneâ€“Oxideâ€“Metal Diode through Biasâ€Induced Barrier Height Modulation. Advanced Electronic Materials, 2016, 2, 1600223.	5.1	25
34	Oxidize Graphene by UV-Ozone Treatment in Vacuum Chamber. Journal of Nanoscience and Nanotechnology, 2016, 16, 7968-7972.	0.9	2
35	Ab initio computation of the transition temperature of the charge density wave transition in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>TiS</mml:mi><mml:msub><mml:mi mathvariant="normal">e</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2015, 92, .	3.2	44
36	Different mechanism of capacitance change for gas detection using semiconducting and metallic single-walled carbon nanotubes. Current Applied Physics, 2015, 15, 377-382.	2.4	1

#	Article	IF	Citations
37	Thin-layer black phosphorus/GaAs heterojunction p-n diodes. Applied Physics Letters, 2015, 106, .	3.3	55
38	Chemically Modulated Band Gap in Bilayer Graphene Memory Transistors with High On/Off Ratio. ACS Nano, 2015, 9, 9034-9042.	14.6	56
39	Graphene/ferroelectrics/graphene hybrid structure: Asymmetric doping of graphene layers. Applied Physics Letters, 2015, 106, .	3.3	13
40	Seamless Stitching of Graphene Domains on Polished Copper (111) Foil. Advanced Materials, 2015, 27, 1376-1382.	21.0	314
41	Direct growth of etch pit-free GaN crystals on few-layer graphene. RSC Advances, 2015, 5, 1343-1349.	3.6	46
42	Confocal absorption spectral imaging of MoS₂: optical transitions depending on the atomic thickness of intrinsic and chemically doped MoS₂. Nanoscale, 2014, 6, 13028-13035.	5.6	319
43	Charge Transport in Polycrystalline Graphene: Challenges and Opportunities. Advanced Materials, 2014, 26, 5079-5094.	21.0	166
44	Transferred wrinkled Al2O3 for highly stretchableÂand transparent grapheneâ€“carbon nanotube transistors. Nature Materials, 2013, 12, 403-409.	27.5	295
45	Nondestructive Characterization of Graphene Defects. Advanced Functional Materials, 2013, 23, 5183-5189.	14.9	44
46	Probing graphene grain boundaries with optical microscopy. Nature, 2012, 490, 235-239.	27.8	352
47	Spectroscopic Determination of the Electrochemical Potentials of n-Type Doped Carbon Nanotubes. Journal of Physical Chemistry C, 2012, 116, 5444-5449.	3.1	17
48	Origin of unipolarity in carbon nanotube field effect transistors. Journal of Materials Chemistry, 2012, 22, 1994-1997.	6.7	14
49	Alumina-coated silicon-based nanowire arrays for high quality Li-ion battery anodes. Journal of Materials Chemistry, 2012, 22, 24618.	6.7	116
50	Band-gap engineering in chemically conjugated bilayer graphene:Ab initiocalculations. Physical Review B, 2012, 85, .	3.2	29
51	Humidity-assisted selective reactivity between NO2 and SO2 gas on carbon nanotubes. Journal of Materials Chemistry, 2011, 21, 4502.	6.7	54
52	Role of Anions in the AuCl₃-Doping of Carbon Nanotubes. ACS Nano, 2011, 5, 1236-1242.	14.6	149
53	Negative and Positive Persistent Photoconductance in Graphene. Nano Letters, 2011, 11, 4682-4687.	9.1	82
54	Facile Physical Route to Highly Crystalline Graphene. Advanced Functional Materials, 2011, 21, 3496-3501.	14.9	97

#	Article	IF	Citations
55	Ultraâ€Transparent, Flexible Singleâ€walled Carbon Nanotube Nonâ€volatile Memory Device with an Oxygenâ€decorated Graphene Electrode. Advanced Materials, 2011, 23, 1889-1893.	21.0	118
56	Transferâ€Free Growth of Fewâ€Layer Graphene by Selfâ€Assembled Monolayers. Advanced Materials, 2011, 23, 4392-4397.	21.0	79
57	Improving the wettability of aluminum on carbon nanotubes. Acta Materialia, 2011, 59, 3313-3320.	7.9	66
58	UV-LIGHT-ASSISTED OXIDATIVE sp3 HYBRIDIZATION OF GRAPHENE. Nano, 2011, 06, 409-418.	1.0	36
59	Carbon Nanotube Doping Mechanism in a Salt Solution and Hygroscopic Effect: Density Functional Theory. ACS Nano, 2010, 4, 5430-5436.	14.6	32
60	Transparent Organic P-Dopant in Carbon Nanotubes: Bis(trifluoromethanesulfonyl)imide. ACS Nano, 2010, 4, 6998-7004.	14.6	56
61	Hygroscopic Effects on AuCl₃-Doped Carbon Nanotubes. Journal of Physical Chemistry C, 2010, 114, 11618-11622.	3.1	33
62	Breaking AB stacking order in graphite oxide: ab initio approach. Physical Chemistry Chemical Physics, 2010, 12, 1595.	2.8	21
63	Reduction-Controlled Viologen in Bisolvent as an Environmentally Stable n-Type Dopant for Carbon Nanotubes. Journal of the American Chemical Society, 2009, 131, 327-331.	13.7	196
64	Defectâ€Engineered Magnetic Field Dependent Optoelectronics of Vanadium Doped Tungsten Diselenide Monolayers. Advanced Optical Materials, 0, , 2102711.	7.3	5